*CLAIM AMENDMENTS*

1. (Currently Amended) A method of fabricating an X-ray mask comprising steps of:

forming an X-ray transmitter; and

forming a laminated X-ray absorber ~~above~~ opposite said X-ray transmitter, wherein said laminated X-ray absorber includes at least two ~~types of~~ layers having different compositions ~~are employed for said laminated X-ray absorber~~.

2. (Currently Amended) The method of fabricating an X-ray mask according to claim 1, wherein

said laminated X-ray absorber includes a first X-ray absorber ~~formed above~~ opposite said X-ray transmitter and a second X-ray absorber ~~formed to be~~ in contact with said first X-ray absorber,

tungsten is employed as ~~the material for~~ one of said first X-ray absorber and said second X-ray absorber, and

diamond is employed as ~~the material for~~ the other ~~one~~ of said first X-ray absorber and said second X-ray absorber.

3. (Currently Amended) The method of fabricating an X-ray mask according to claim 1, wherein said laminated X-ray absorber includes a first X-ray absorber ~~formed~~ on said X-ray transmitter and a second X-ray absorber ~~formed~~ on said first X-ray absorber, and the ~~said~~ method of fabricating an X-ray mask further ~~comprising steps of~~ comprises:

forming ~~a film serving as~~ an etching stopper film, stopping etching when etching said first X-ray absorber on said X-ray transmitter, and

forming said second X-ray absorber on said ~~film serving as an~~ etching stopper film.

4. (Currently Amended) The method of fabricating an X-ray mask according to claim 1, wherein said laminated X-ray absorber includes a first X-ray absorber ~~formed above~~ opposite said X-ray transmitter and a second X-ray absorber ~~formed~~ on said first X-ray absorber, ~~said~~ and the method of fabricating an X-ray mask further ~~comprising steps of~~ comprises:

forming an interlayer film ~~having either a function for serving~~ as an etching stopper or ~~a function for serving as~~ a hard mask on said first X-ray absorber, and

forming said second X-ray absorber on said interlayer film.

5. (Currently Amended) The method of fabricating an X-ray mask according to claim 1, wherein said laminated X-ray absorber has a layer containing at least one substance selected from ~~a~~ the group consisting of lithium ~~(Li)~~, beryllium ~~(Be)~~, boron ~~(B)~~, carbon ~~(C)~~,

sodium ~~(Na)~~, magnesium ~~(Mg)~~, aluminum ~~(Al)~~, silicon ~~(Si)~~, phosphorus ~~(P)~~, sulfur ~~(S)~~, potassium ~~(K)~~, calcium ~~(Ca)~~, scandium ~~(Sc)~~, titanium ~~(Ti)~~, vanadium ~~(V)~~, chromium ~~(Cr)~~, manganese ~~(Mn)~~, iron ~~(Fe)~~, cobalt ~~(Co)~~, nickel ~~(Ni)~~, copper ~~(Cu)~~, zinc ~~(Zn)~~, gallium ~~(Ga)~~, germanium ~~(Ge)~~, arsenic ~~(As)~~, selenium ~~(Se)~~, palladium ~~(Pd)~~, silver ~~(Ag)~~, cadmium ~~(Cd)~~, indium ~~(In)~~, tin ~~(Sn)~~, antimony ~~(Sb)~~, tellurium ~~(Te)~~, cesium ~~(Cs)~~, barium ~~(Ba)~~, mixtures of these elements, a carbide including silicon carbide ~~or~~ and tungsten carbide, a nitride ~~such as~~ including silicon nitride, aluminum nitride, ~~or~~ and chromium nitride, an oxide including silicon oxide ~~or~~ and chromium oxide, a fluoride, and an iodide.

6. (Currently Amended) The method of fabricating an X-ray mask according to claim 1, wherein said laminated X-ray absorber has a layer containing a substance selected from ~~a~~ the group consisting of carbon ~~(C)~~, titanium ~~(Ti)~~, vanadium ~~(V)~~, chromium ~~(Cr)~~, manganese ~~(Mn)~~, iron ~~(Fe)~~, nickel ~~(Ni)~~, copper ~~(Cu)~~, zinc ~~(Zn)~~, gallium ~~(Ga)~~, germanium ~~(Ge)~~, arsenic ~~(As)~~, selenium ~~(Se)~~, palladium ~~(Pd)~~, silver ~~(Ag)~~, cadmium ~~(Cd)~~, indium ~~(In)~~, tin ~~(Sn)~~, antimony ~~(Sb)~~, and tellurium ~~(Te)~~.

7. (Currently Amended) A method of fabricating an X-ray mask comprising ~~steps of~~:

forming a ~~dug~~ removed portion ~~and~~ on an X-ray transmitter, leaving a portion other than said ~~dug~~ removed portion on ~~an~~ said X-ray transmitter; and

forming an X-ray absorber on said portion other than said ~~dug~~ removed portion.

8. (Currently Amended) The method of fabricating an X-ray mask according to claim 7 further comprising ~~a step of performing ion implantation~~ implanting ions into said X-ray transmitter before forming said ~~dug~~ removed portion.

9. (Currently Amended) The method of fabricating an X-ray mask according to claim 1, wherein ~~said step of~~ forming said X-ray absorber includes ~~steps of~~:

forming an X-ray transmitter;

forming a first X-ray absorber ~~above~~ opposite said X-ray transmitter; and

forming a second X-ray absorber, different in pattern size from said first X-ray absorber, on said first X-ray absorber.

10. (Currently Amended) The method of fabricating an X-ray mask according to claim 9, wherein the pattern size of said first X-ray absorber is larger than the pattern size of said second X-ray absorber.

11. (Currently Amended) A method of fabricating a semiconductor device including carrying out an exposure ~~step~~ with an X-ray mask ~~on condition that~~ having a geometric X-ray phase difference between the phase of X-rays transmitted through an X-ray transmission part of said X-ray mask and the phase of X-rays transmitted through an X-ray absorber of said X-ray ~~mask is~~ in ~~the~~ a range including $0.5\pi$ and ~~in~~ proximity to $0.5\pi$, between a resist film located ~~on~~ at a position for forming an optical image with said X-rays and said X-ray mask, wherein

said X-ray mask comprises an X-ray transmitter and said X-ray absorber ~~consisting of~~ includes a laminated structure having at least two layers ~~formed~~ on said X-ray transmitter,

said laminated structure includes at least two layers having different compositions, and

~~at least~~ either ~~a condition that~~ the phase shift ~~quantity~~ of ~~said~~ the X-rays transmitted through said X-ray absorber is in ~~the~~ a range of $0.3\pi$ to $0.6\pi$ or ~~a condition that~~ the transmittance of ~~said~~ the X-rays transmitted through said X-ray absorber is in ~~the~~ a range of 30 % to 60 % ~~holds~~.

12. (Currently Amended) The method of fabricating a semiconductor device according to claim 11, including carrying out ~~said~~ the exposure ~~step~~ on condition that an average exposure wavelength of the X-rays is longer than 0.3 nm and shorter than 0.7 nm.

13. (Currently Amended) The method of fabricating a semiconductor device according to claim 11, wherein ~~the~~ absolute value of ~~the~~ a difference between ~~said~~ the geometric phase difference and ~~said~~ the phase shift quantity is in ~~the~~ a range including $\pi$ and ~~in~~ proximity to $\pi$.